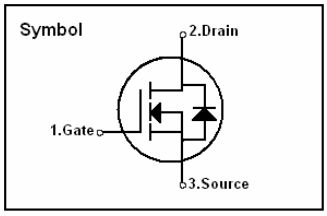
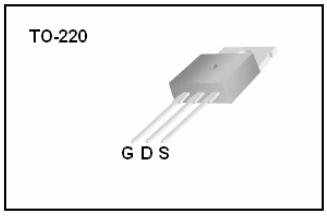
200V N-Channel MOSFET

Features

- 18A,200v,RDS(on)=0.18Ω@VGS=10V
- Gate charge (Typical 44nC)
- High ruggedness
- Fast switching
- 100% AvalancheTested
- Improved dv/dt capability





General Description

This Power MOSFET is produced using Truesemi's advanced planar stripe, DMOS technology.
This latest technology has been especially designed to minimize on-state resistance,have a high rugged avalanche characteristics. These devices are well suited for low voltage application such as automotive,DC/DC converters,and high efficiency switch for power management in portable and battery products.

Absolute Maximum Ratings

Symbol	Parameter		Value	Units
VDSS	Drain to Source Voltage		200	V
ID	Continuous Drain Current(@TC = 25°C)		18*	A
	Continuous Drain Current(@TC = 100°C)		11*	A
IDM	Drain Current Pulsed	(Note 1)	72*	A
VGS	Gate to Source Voltage		±30	V
EAS	Single Pulsed Avalanche Energy	(Note 2)	220	mJ
EAR	Repetitive Avalanche Energy	(Note 1)	13.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
PD	Total Power Dissipation(@TC = 25 °C)		135	W
	Derating Factor above 25 °C		1.11	W/°C
TSTG, TJ	Operating Junction Temperature & Storage Temperature		-55 ~ 150	°C
TL	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.		300	°C

Thermal Characteristics

Symbol	Parameter	Value			Units
		Min.	Typ.	Max.	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	-	-	0.9	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ	-	0.5	-	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	-	62.5	°C/W

Electrical Characteristics (TC = 25 °C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250uA	200	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature coefficient	I_D = 250uA, referenced to 25°C	-	0.26	-	V/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS} = 200V, V_{GS} = 0V	-	-	1	uA
		V_{DS} = 160V, T_C = 150 °C	-	-	10	uA
I_{GSS}	Gate-Source Leakage, Forward	V_{GS} = 30V, V_{DS} = 0V	-	-	100	nA
	Gate-source Leakage, Reverse	V_{GS} =-30V, V_{DS} = 0V	-	-	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250uA	2.0	-	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-state Resistance	V_{GS} =10 V, I_D = 9A	-	0.15	0.18	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} =0 V, V_{DS} =25V, f = 1MHz	-	1010	1300	pF
C_{oss}	Output Capacitance		-	190	240	
C_{rss}	Reverse Transfer Capacitance		-	80	110	
Dynamic Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} =100V, I_D =18A, R_G =25Ω	-	15	30	ns
t_r	Rise Time		-	80	150	
$t_{d(off)}$	Turn-off Delay Time		-	50	90	
t_f	Fall Time		-	60	120	
Q_g	Total Gate Charge	V_{DS} =160V, V_{GS} =10V, I_D =18A	-	44	55	nC
Q_{gs}	Gate-Source Charge		-	10	-	
Q_{gd}	Gate-Drain Charge(Miller Charge)		-	18	-	

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
I_S	Continuous Source Current	Integral Reverse p-n Junction Diode in the MOSFET	-	-	18	A
I_{SM}	Pulsed Source Current		-	-	72	
V_{SD}	Diode Forward Voltage	I_S =18A, V_{GS} =0V	-	-	1.5	V
t_{rr}	Reverse Recovery Time	I_S=18A,V_{GS}=0V, dI_F/dt=100A/us	-	190	-	ns
Q_{rr}	Reverse Recovery Charge		-	1.3	-	uC

※ NOTES

1. Repeativity rating : pulse width limited by junction temperature
2. L =1muH, I_{AS} = 18A, V_{DD} = 50V, R_G = 50Ω , Starting T_J = 25°C
3. I_{SD} ≤ 18A, di/dt ≤ 300A/us, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse Width ≤ 300us, Duty Cycle ≤ 2%
5. Essentially independent of operating temperature.

Fig 1. On-State Characteristics

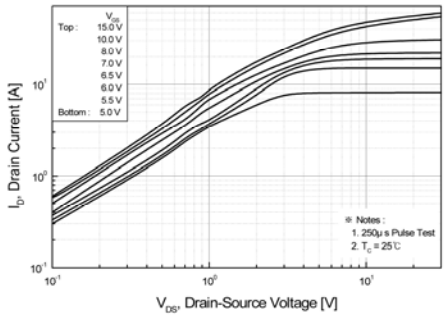


Fig 2. Transfer Characteristics

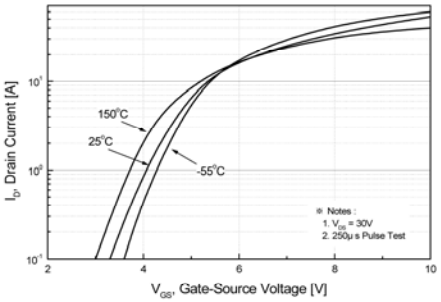


Fig 3. On Resistance Variation vs. Drain Current and Gate Voltage

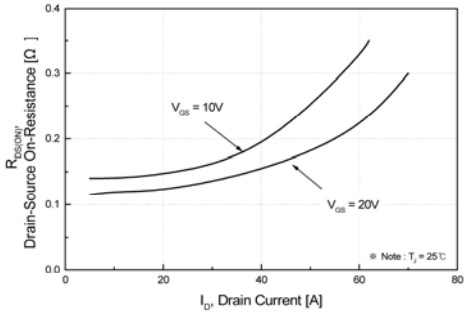


Fig 4. On State Current vs. Allowable Case Temperature

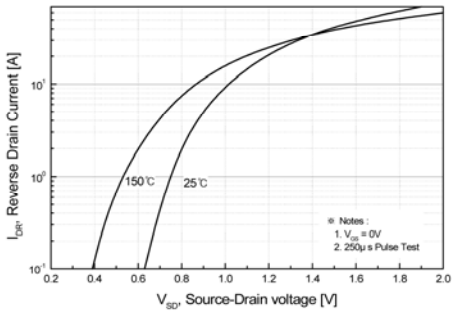


Fig 5. Capacitance Characteristics

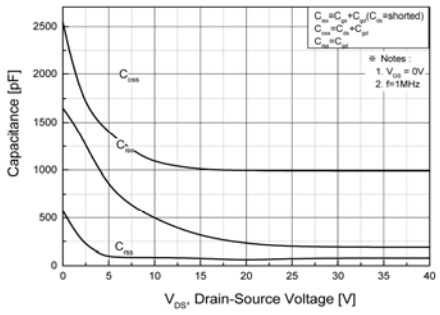


Fig 6. Gate Charge Characteristics

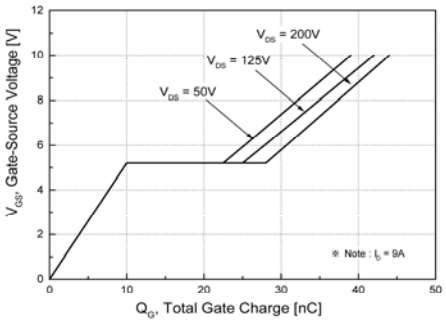


Fig 7. Breakdown Voltage Variation vs. Junction Temperature

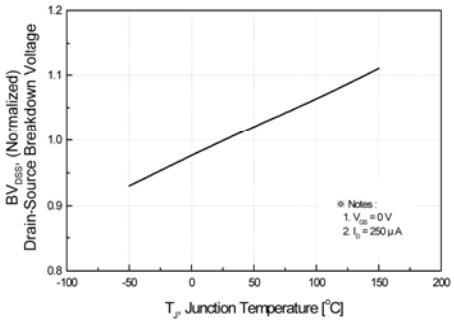


Fig 8. On-Resistance Variation vs. Junction Temperature

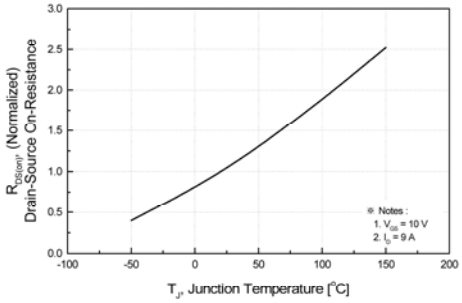


Fig 9. Maximum Safe Operating Area

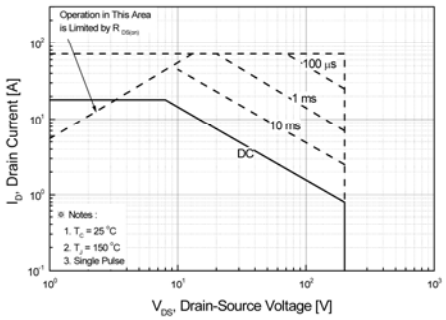


Fig 10. Maximum Drain Current vs. Case Temperature

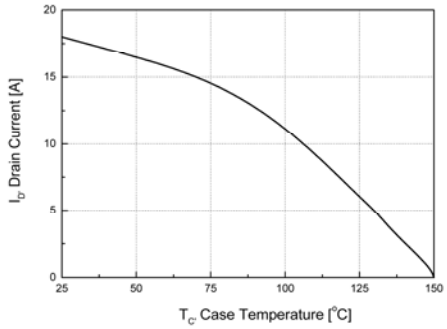


Fig 11. Transient Thermal Response Curve

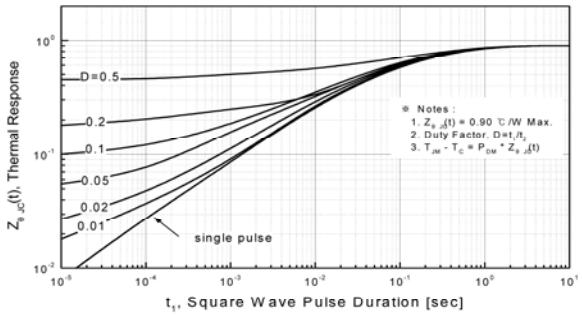


Fig. 12. Gate Charge Test Circuit & Waveforms

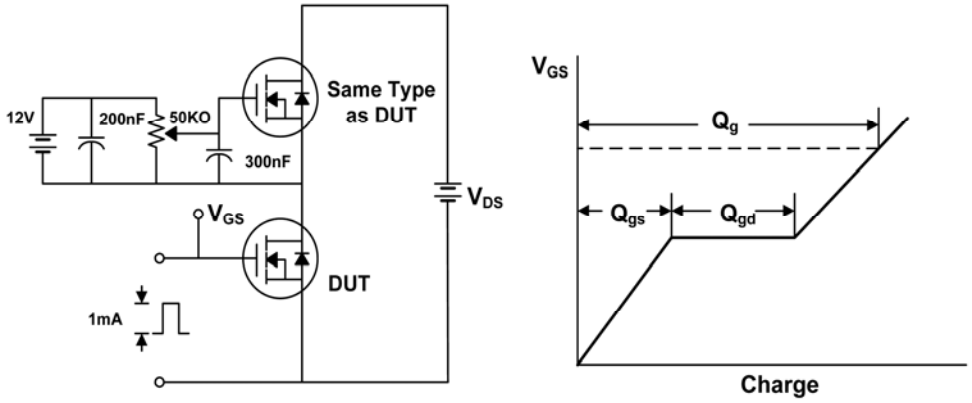


Fig 13. Switching Time Test Circuit & Waveforms

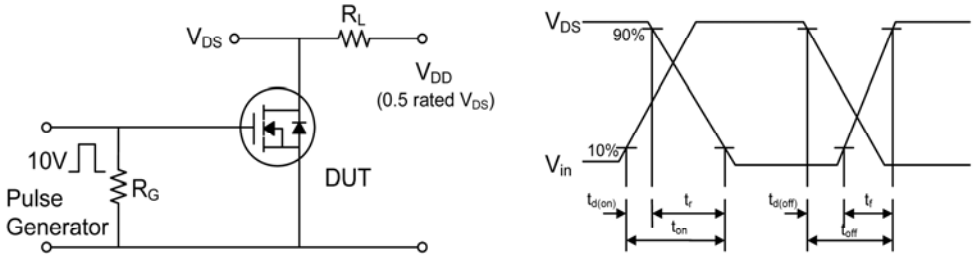


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

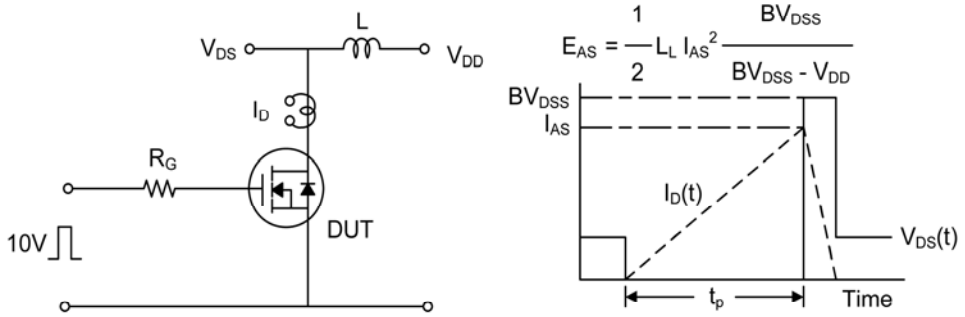
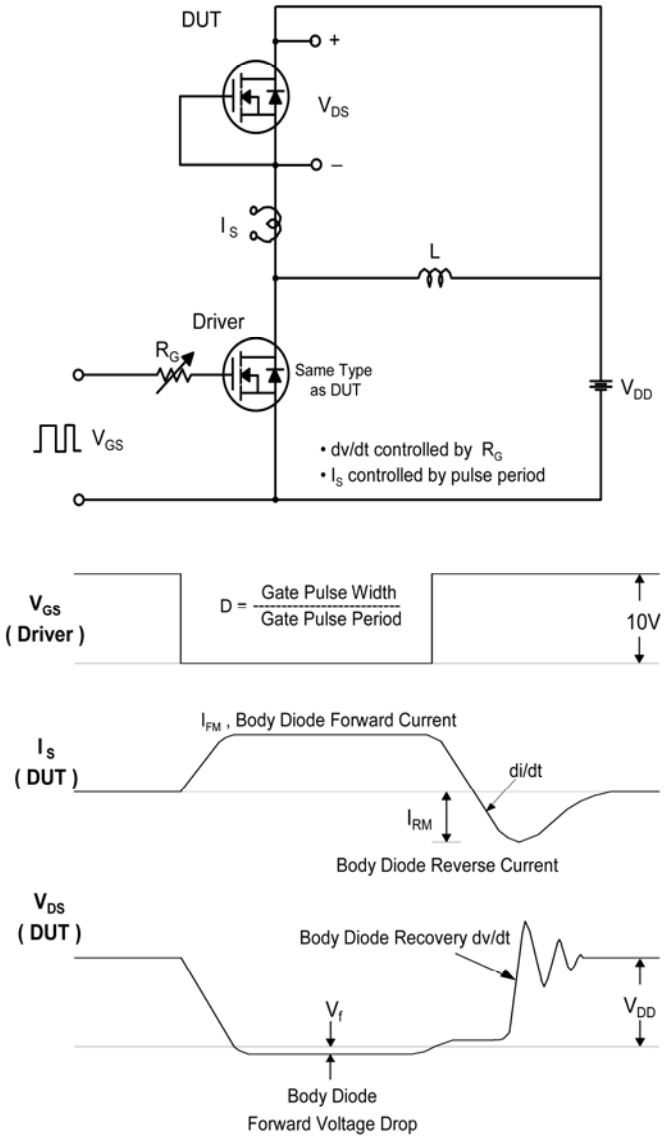
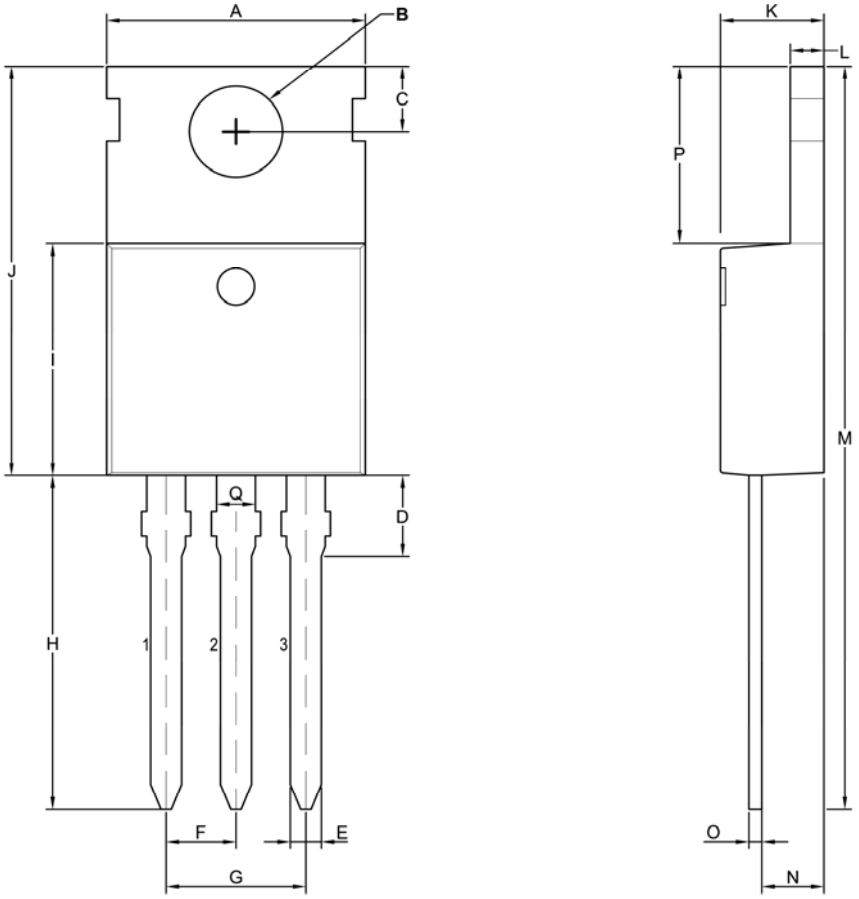


Fig. 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220



TO-220 DIMENSION			
Symbol	Dimensions In Millimeters		
	Min	Max	Typ
A	10.10	10.35	10.25
B	3.75	3.85	3.80
C	2.50	2.90	2.75
D	3.70	4.50	4.10
E	0.70	0.90	0.80
F	—	—	2.54
G	—	—	5.08
H	13.50	14.20	13.80
I	8.50	9.00	8.80
J	14.80	15.20	15.00
K	4.50	4.58	4.54
L	1.28	1.36	1.32
M	28.60	29.10	28.90
N	2.40	2.90	2.65
O	0.38	0.45	0.40
P	6.20	6.60	6.40
Q	1.30	1.45	1.40